7. (Amended) The hot plate according to claim 1, wherein said resistance element has a multilayer structure, and among a plurality of layers constituting said resistance element, the layer nearest to the substrate is made of titanium or chromium.

8. (Amended) The hot plate according to claim 1, wherein said resistance element is composed of a first layer made of titanium; a second layer made of molybdenum and having a larger thickness than said first layer, on said first layer; and a third layer made of nickel and having an intermediate thickness between the thickness of said first layer and that of said second layer, on said second layer.

9. (Amended) The hot plate according to claim 1, wherein said resistance element is composed of a titanium layer having a thickness of 0.1 to 0.5 μm, a molybdenum layer having a thickness of 0.5 to 7.0 μm, on said titanium layer, and a nickel layer having a thickness of 0.4 to 2.5 μm, on said molybdenum layer.

13. (Amended) The hot plate according to claim 1, wherein said resistance element is formed on the lower face of the insulating substrate.

Please add the following new claims:

14. (New) A process for producing a hot plate wherein a resistance element having a thickness dispersion of ±3 μm or less is formed on an insulating substrate,

comprising forming said resistance element by a film-depositing method based on a dry process.

15. (New) A process for producing a hot plate wherein a resistance element having a thickness dispersion of ±3 μm or less is formed on an insulating substrate,

comprising forming said resistance element by RF sputtering.

16. (New) A process for producing a hot plate wherein a resistance element having a thickness dispersion of ±3 μm or less is formed on an insulating substrate,